



# STF3NK100Z - STD3NK100Z STP3NK100Z

N-channel 1000V - 5.4Ω - 2.5A - TO-220 - TO-220FP - DPAK  
Zener-protected SuperMESH™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub>	P <sub>TOT</sub>
STF3NK100Z	1000V	< 6Ω	2.5A	25W
STP3NK100Z	1000V	< 6Ω	2.5A	90W
STD3NK100Z	1000V	< 6Ω	2.5A	90W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

## Application

- Switching applications

## Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, specialties is taken to ensure a very good dv/dt capability for the most demanding application. Such series complements ST full range of high voltage Power MOSFETs.

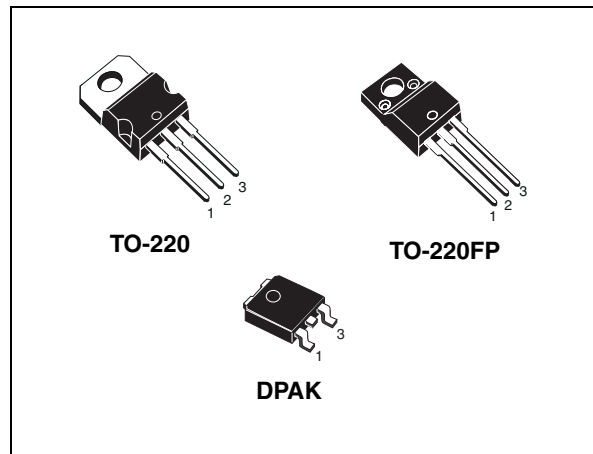


Figure 1. Internal schematic diagram

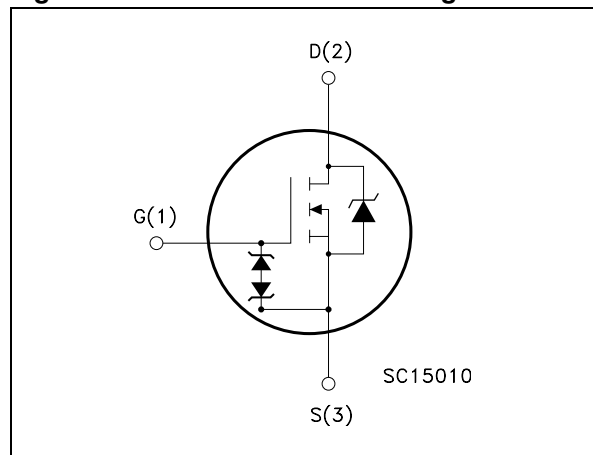


Table 1. Device summary

Order codes	Marking	Package	Packaging
STF3NK100Z	F3NK100Z	TO-220FP	Tube
STP3NK100Z	P3NK100Z	TO-220	Tube
STD3NK100Z	D3NK100Z	DPAK	Tape & reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>14</b>
<b>6</b>	<b>Revision history</b> .....	<b>15</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220/DPAK	TO-220FP	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	1000		V
$V_{GS}$	Gate-source voltage	$\pm 30$		V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	2.5	2.5 <sup>(1)</sup>	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	1.57	1.57 <sup>(2)</sup>	A
$I_{DM}^{(2)}$	Drain current (pulsed)	10	10 <sup>(2)</sup>	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	90	25	W
	Derating factor	0.72	0.2	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD (HBM-C=100pF, R=1.5K $\Omega$ )	3000		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5		V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t=1s; T_C=25^\circ\text{C}$ )	--	2500	V
$T_j$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150		$^\circ\text{C}$

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 2.5\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value		Unit
		TO-220/DPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.39	5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5		$^\circ\text{C}/\text{W}$
$T_L$	Maximum lead temperature for soldering purpose	300		

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not-repetitive	2.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ

- Pulse width limited by  $T_{jmax}$
- Starting  $T_j = 25^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{V}$

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 5. On/off**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	1000			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$			1 50	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 10$	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 50\mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 1.25A$		5.4	6	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 1.25A$		2.4		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		601 53 12		pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 800V$		15		pF
$R_G$	Gate input resistance	$f = 1 \text{ MHz}, \text{ open drain}$		8.6		$\Omega$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 800V, I_D = 2.5A$ $V_{GS} = 10V$ (see Figure 17)		18 3.6 9.2		nC nC nC

1. Pulsed: pulse duration = 300 $\mu s$ , duty cycle 1.5%

2.  $C_{oss \text{ eq.}}$  is defined as constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD}=500V$ , $I_D=1.25A$ , $R_G=4.7\Omega$ , $V_{GS}=10V$ (see Figure 16)		15 7.5		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD}=500V$ , $I_D=1.25A$ , $R_G=4.7\Omega$ , $V_{GS}=10V$ (see Figure 16)		39 32		ns ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				2.5 10	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=2.5A$ , $V_{GS}=0$			1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=2.5A$ , $di/dt=100A/\mu s$ , $V_{DD}=100V$ , $T_j=25^\circ C$ (see Figure 21)		584 2.3 8		ns $\mu C$ A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=2.5A$ , $di/dt=100A/\mu s$ , $V_{DD}=100V$ , $T_j=150^\circ C$ (see Figure 21)		628 2.5 8.1		ns $\mu C$ A

1. Pulse width limited by package
2. Pulsed: pulse duration = 300 $\mu s$ , duty cycle 1.5%

**Table 9. Gate-source zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{GS}=\pm 1mA$ (open drain)	30			V

1. The built in back-to-back zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220/ DPAK

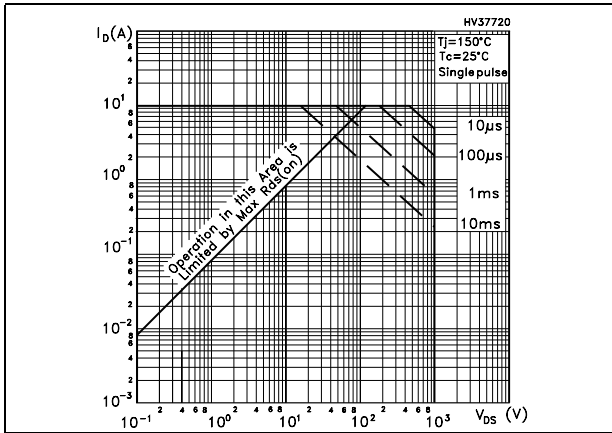


Figure 3. Thermal impedance for TO-220/ DPAK

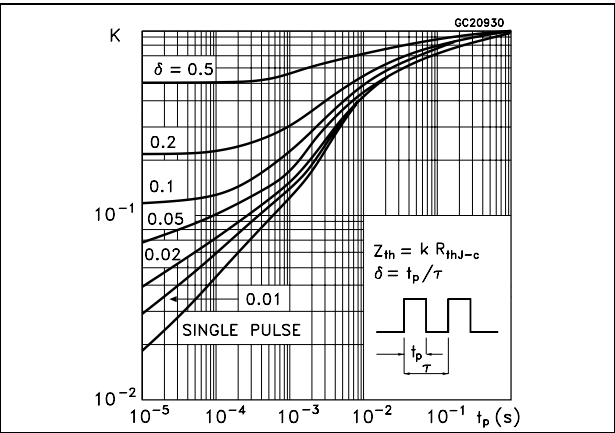


Figure 4. Safe operating area for TO-220FP

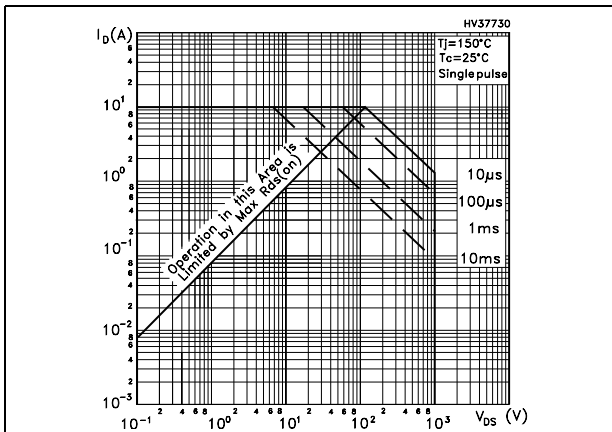


Figure 5. Thermal impedance for TO-220FP

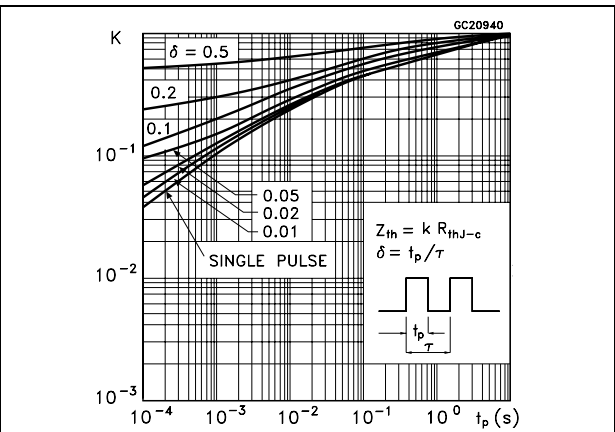


Figure 6. Output characteristics

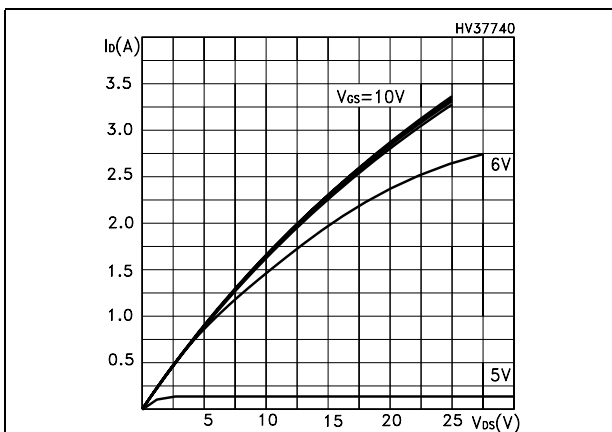


Figure 7. Transfer characteristics

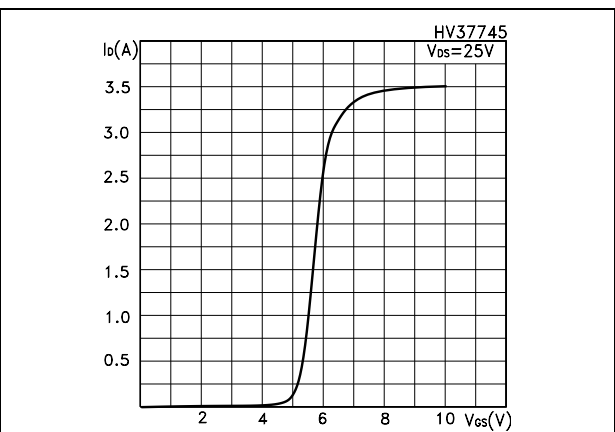


Figure 8. Normalized  $V_{DSS}$  vs. temperature      Figure 9. Static drain-source on resistance

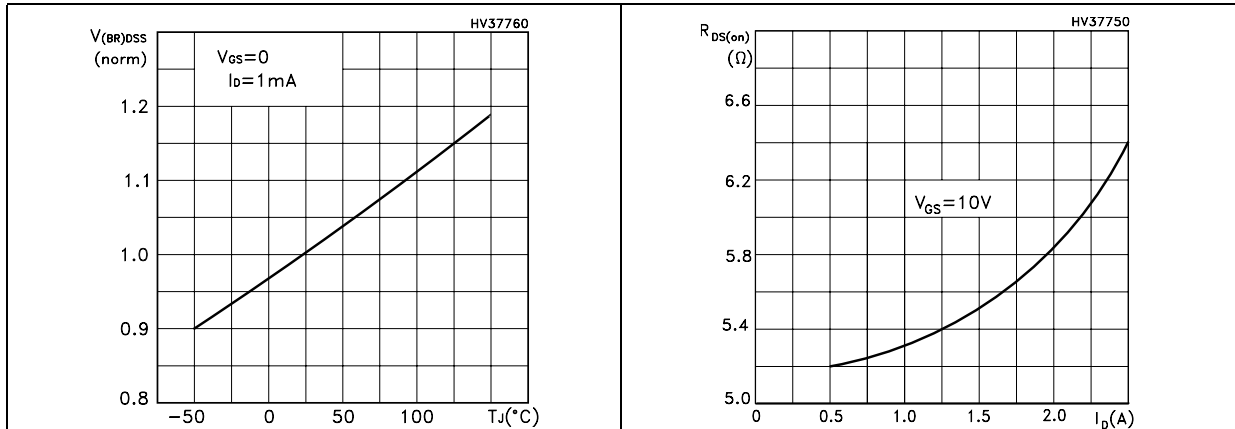


Figure 10. Gate charge vs. gate-source voltage      Figure 11. Capacitance variations

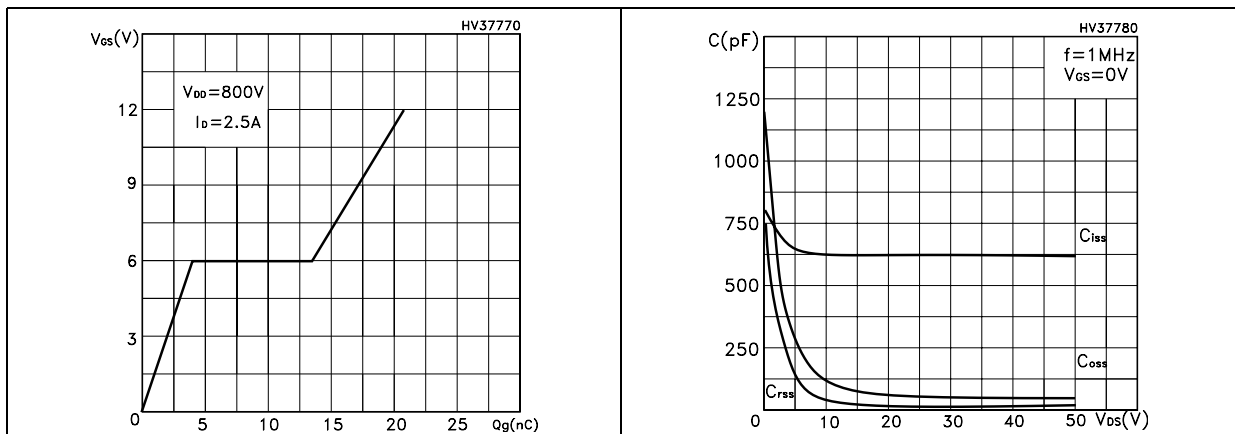


Figure 12. Normalized gate threshold voltage vs. temperature      Figure 13. Normalized on resistance vs. temperature

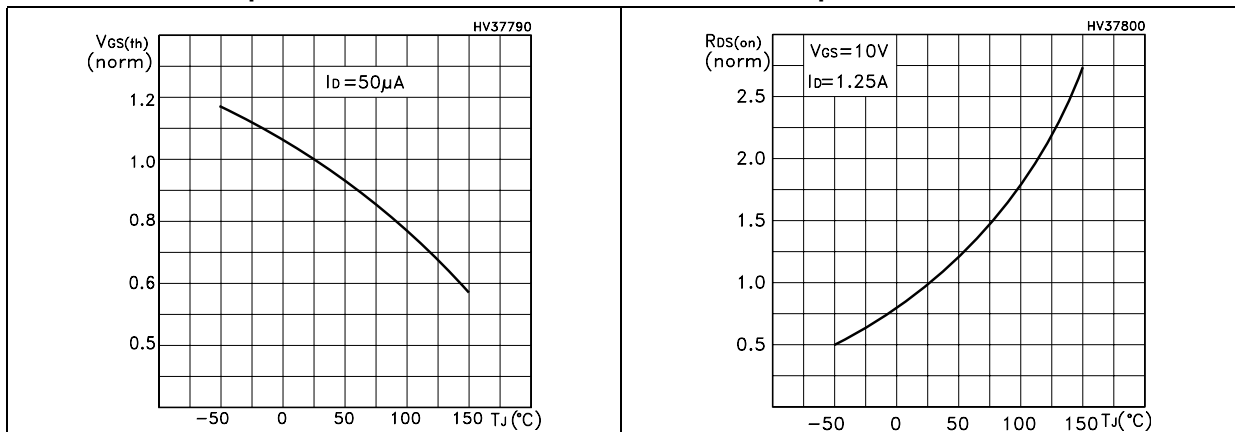


Figure 14. Source-drain diode forward characteristics

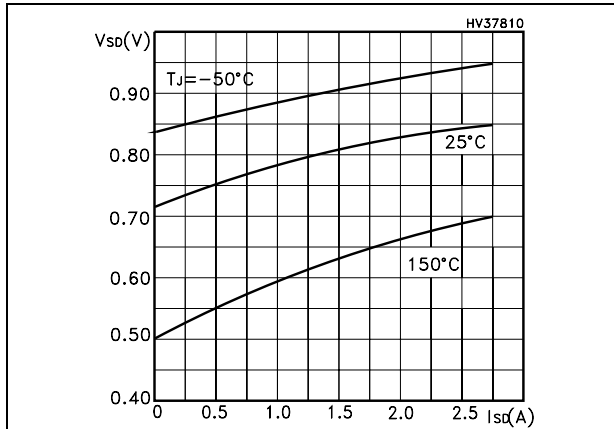
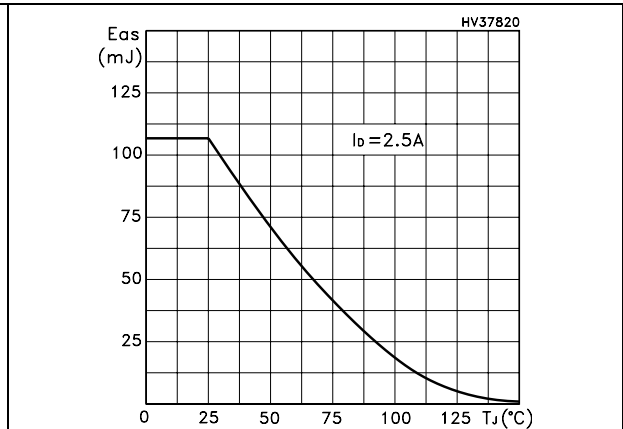


Figure 15. Maximum avalanche energy vs  $T_J$





### 3 Test circuits

Figure 16. Switching times test circuit for resistive load

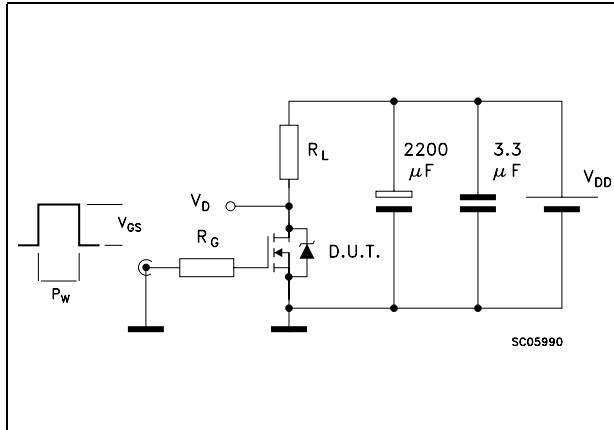


Figure 17. Gate charge test circuit

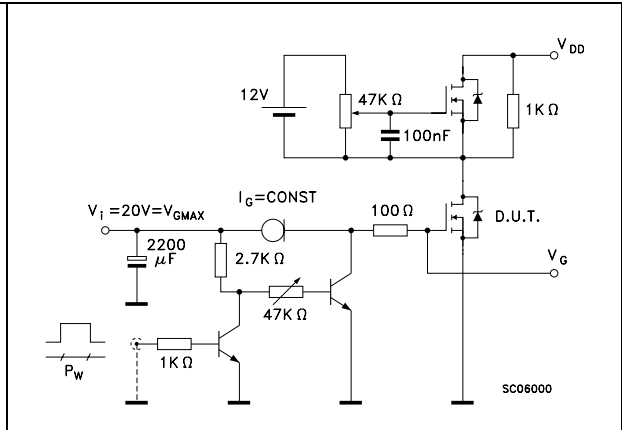


Figure 18. Test circuit for inductive load switching and diode recovery times

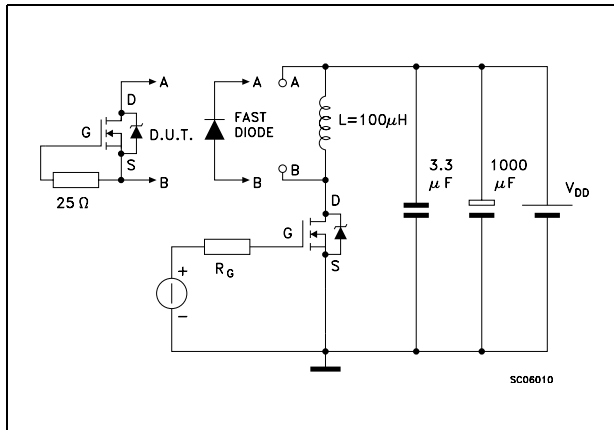


Figure 19. Unclamped inductive load test circuit

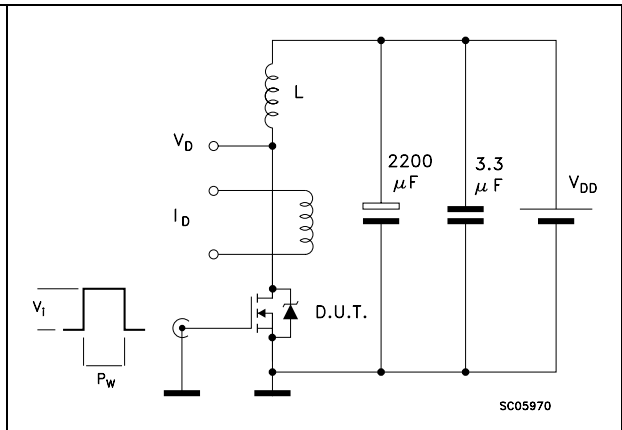


Figure 20. Unclamped inductive waveform

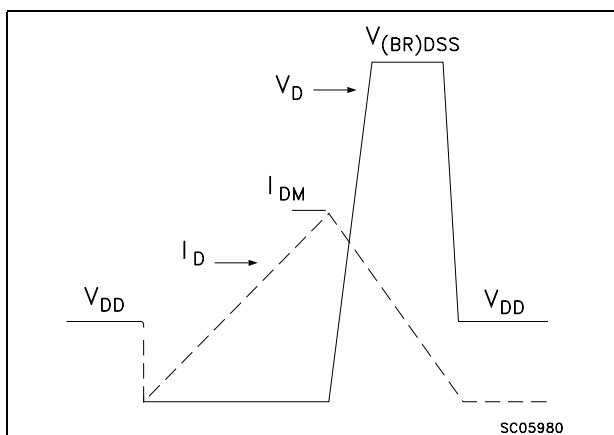
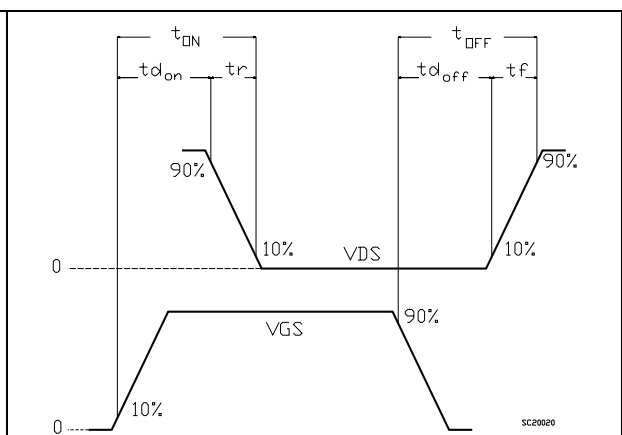


Figure 21. Switching time waveform

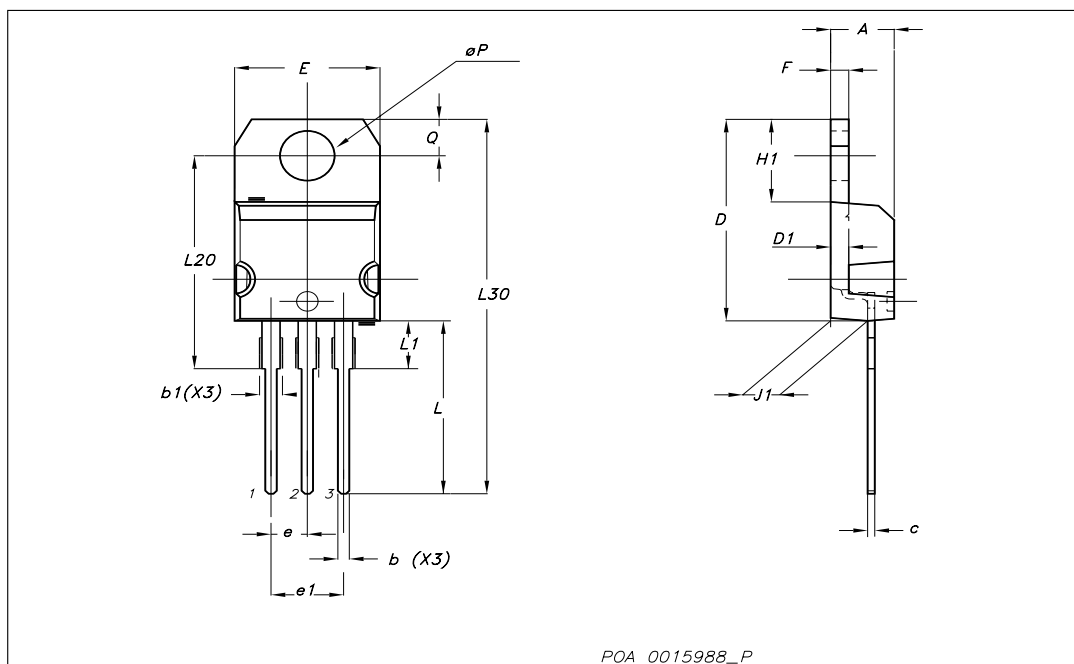


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

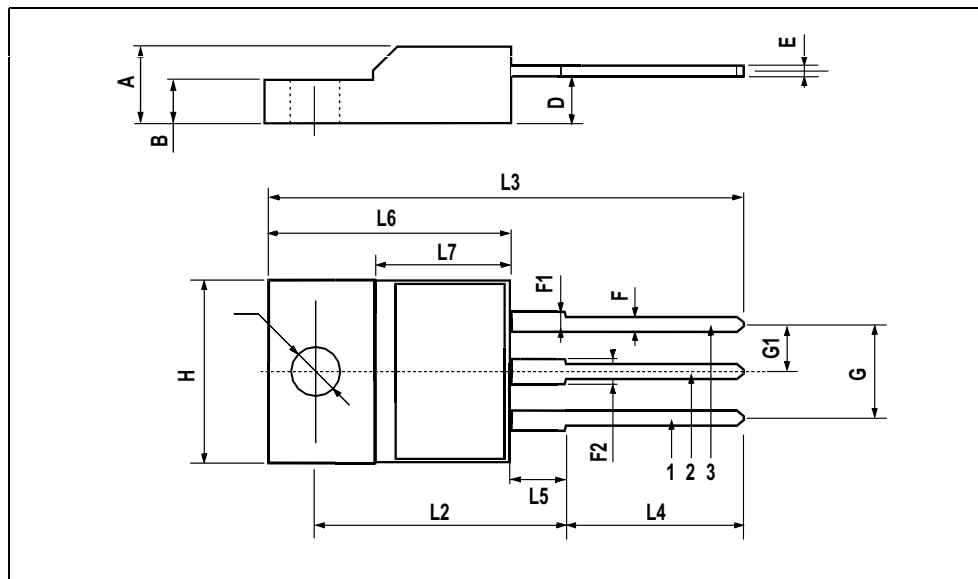
## TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



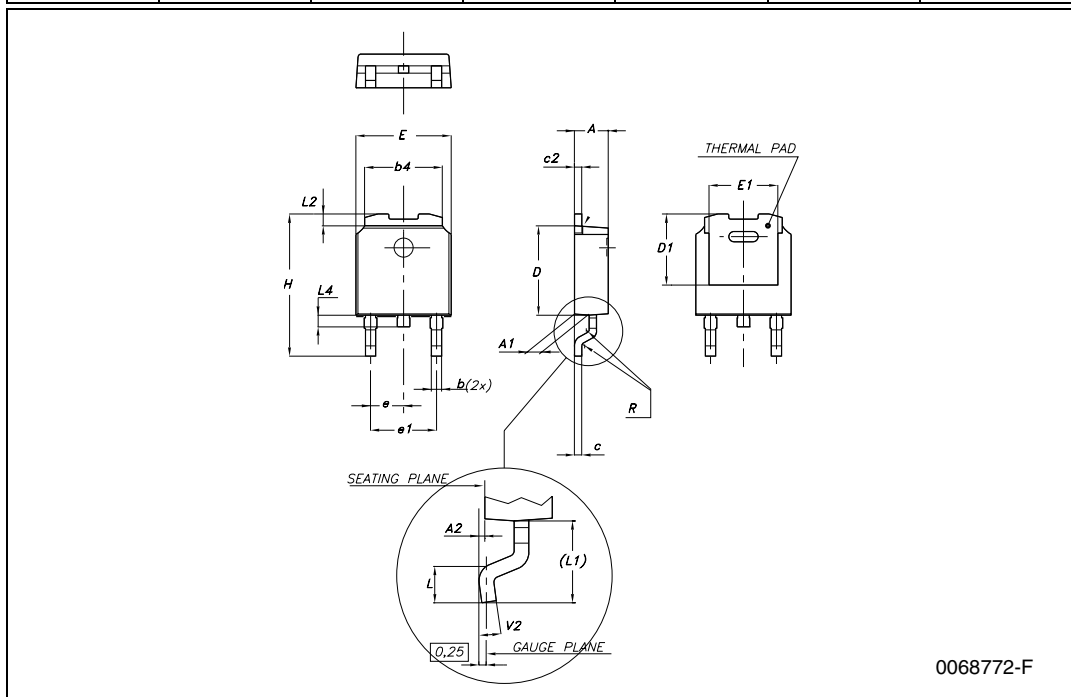
**TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



**DPAK MECHANICAL DATA**

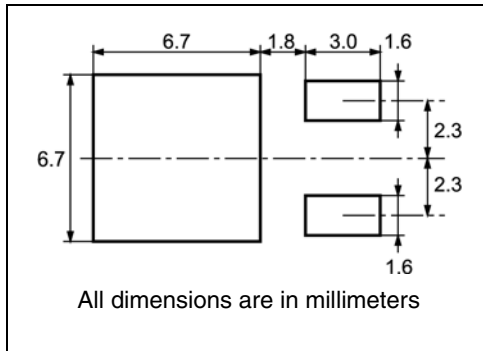
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



0068772-F

# 5 Packaging mechanical data

## DPAK FOOTPRINT



## TAPE AND REEL SHIPMENT

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

## 6 Revision history

Table 10. Document revision history

Date	Revision	Changes
17-May-2007	1	First release
18-Oct-2007	2	Added DPAK

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